

FEATURES

- Double Side Cooling
- High Surge Capability
- Low Inductance Internal Construction

KEY PARAMETERS

V_{DRM}	1800V
$I_{T(AV)}$	5985A
I_{TSM}	98000A
dV/dt^*	1000V/μs
dI/dt	250A/μs

APPLICATIONS

- High Voltage Power Converters
- DC Motor Control
- High Voltage Power Supplies

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} V	Conditions
DCR5980A18	1800	$T_{vj} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$, $I_{DRM} = I_{RRM} = 500\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR5980A16	1600	
DCR5980A14	1400	
DCR5980A12	1200	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5980A14

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

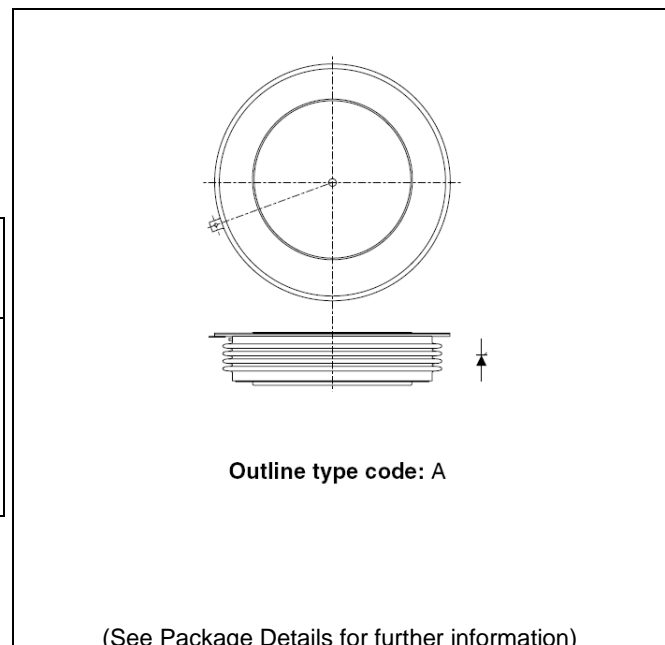


Fig. 1 Package outline

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	5985	A
I _{T(RMS)}	RMS value	-	9400	A
I _T	Continuous (direct) on-state current	-	8400	A
Single Side Cooled (Anode side)				
I _{T(AV)}	Mean on-state current	Half wave resistive load	3820	A
I _{T(RMS)}	RMS value	-	6000	A
I _T	Continuous (direct) on-state current	-	4920	A

T_{case} = 80°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	4650	A
I _{T(RMS)}	RMS value	-	7300	A
I _T	Continuous (direct) on-state current	-	6360	A
Single Side Cooled (Anode side)				
I _{T(AV)}	Mean on-state current	Half wave resistive load	2910	A
I _{T(RMS)}	RMS value	-	4570	A
I _T	Continuous (direct) on-state current	-	3630	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$ $V_R = 50\%V_{RRM} - \frac{1}{4}$ Sine	78.0	kA
I^2t	I^2t for fusing		30.4×10^6	A^2s
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$ $V_R = 0$	98.0	kA
I^2t	I^2t for fusing		48×10^6	A^2s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0065	$^{\circ}C/W$
		Single side cooled	Anode DC	-	0.013	$^{\circ}C/W$
			Cathode DC	-	0.013	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 83.0kN (with mounting compound)	Double side	-	0.001	$^{\circ}C/W$
			Single side	-	0.002	$^{\circ}C/W$
T_{vj}	Virtual junction temperature	On-state (conducting)		-	135	$^{\circ}C$
		Reverse (blocking)		-	125	$^{\circ}C$
T_{stg}	Storage temperature range			-55	125	$^{\circ}C$
F_m	Clamping force			74.0	91.0	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	500	mA	
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open	-	1000	V/ μ s	
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1100A Gate source 20V, 20 Ω , $t_r = 0.5\mu$ s to 1A, $T_j = 125^{\circ}C$	Repetitive 50Hz	-	250	A/ μ s
			Non-repetitive	-	500	A/ μ s
$V_{T(TO)}$	Threshold voltage – Low level	At $T_{vj} = 125^{\circ}C$	-	0.77	V	
r_T	On-state slope resistance – Low level	At $T_{vj} = 125^{\circ}C$	-	0.05	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 15 Ω $t_r = 0.5\mu$ s, $T_j = 25^{\circ}C$	1.0	1.5	μ s	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$	150	750	mA	
I_H	Holding current	$T_j = 25^{\circ}C$, $V_{G-K} = \infty$	40	200	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.5	V
V_{GD}	Gate non-trigger voltage	At V_{DRM} , $T_{case} = 125^{\circ}C$	0.25	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	500	mA
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak forward gate voltage	-	5	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	30	A
P_{GM}	Peak gate power	See Gate Characteristics curve/table	150	W
$P_{G(AV)}$	Mean gate power	-	10	W

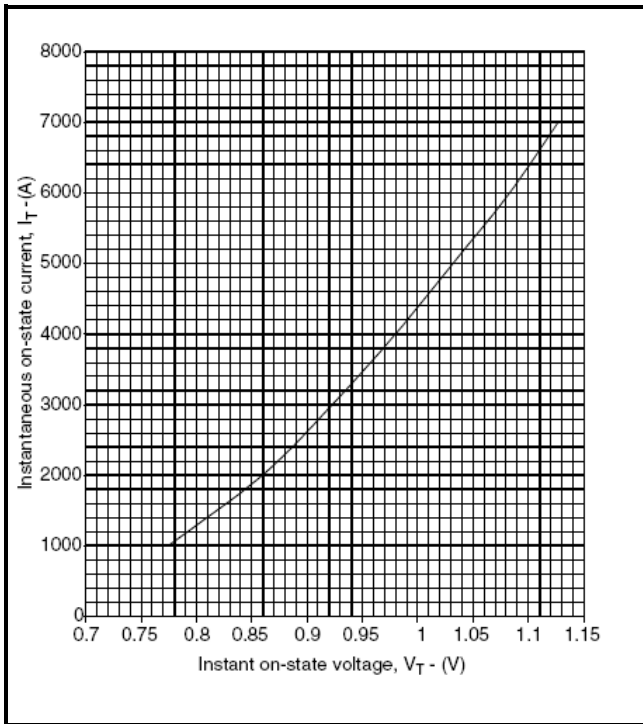


Fig.2 Maximum (limit) on-state characteristics

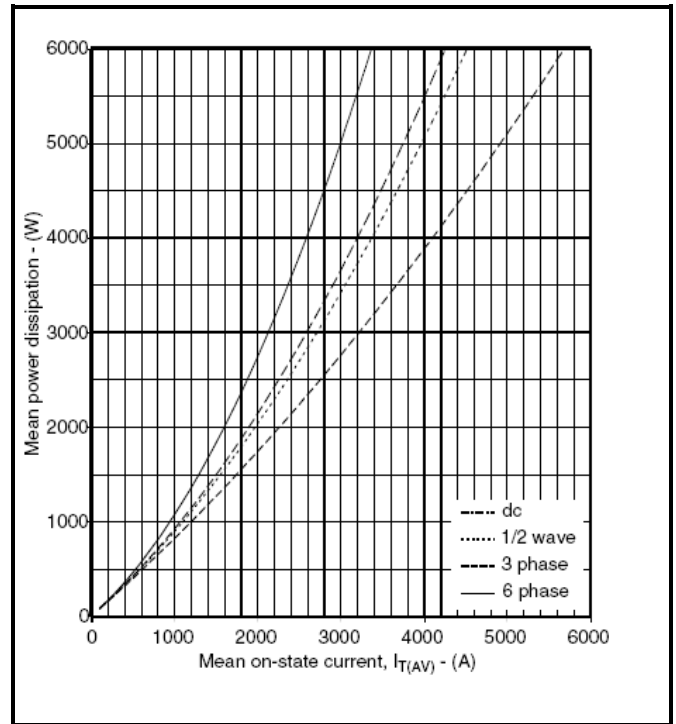


Fig.3 Power dissipation curves

V_{TM} Equation:-

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where

A = 0.4624

B = 0.0275

C = 2.2501×10^{-5}

D = 0.0032

these values are valid for $T_j = 125^\circ\text{C}$ for I_T 500A to 7000A

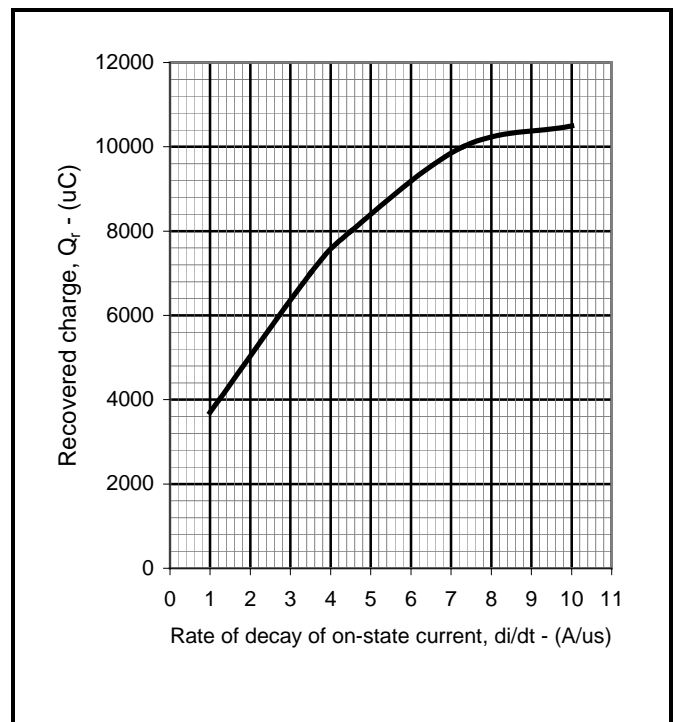


Fig.4 Recovered charge

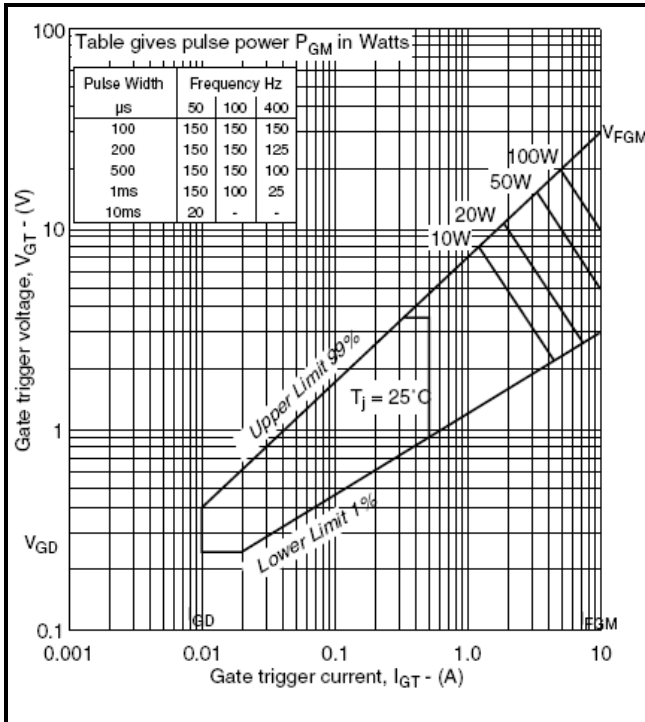


Fig.5 Gate characteristics

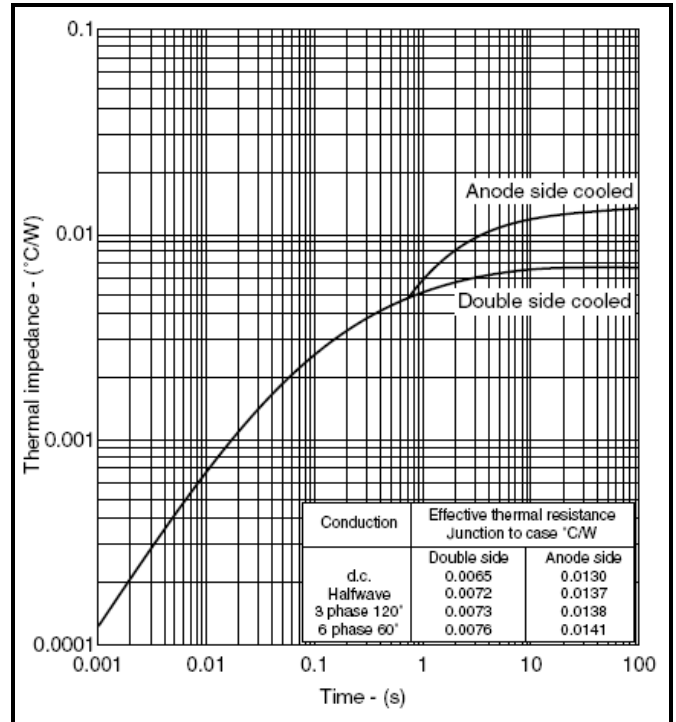


Fig.6 Maximum (limit) transient thermal impedance- junction to case ($^\circ\text{C/W}$)

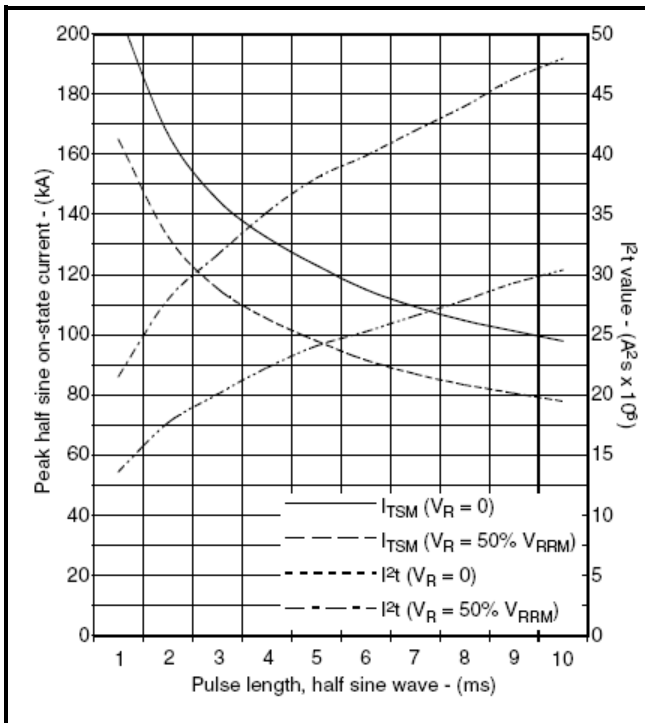


Fig.7 Sub-cycle surge current

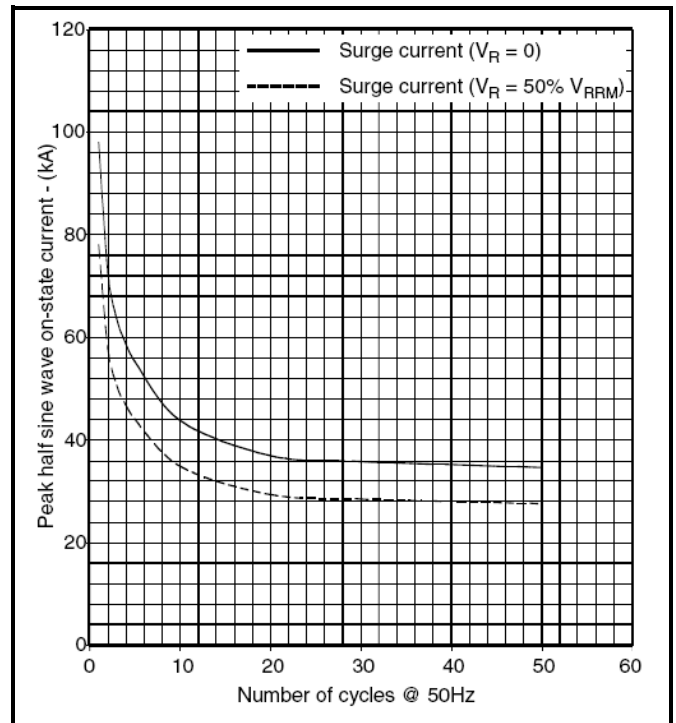


Fig.8 Multi-cycle surge current

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

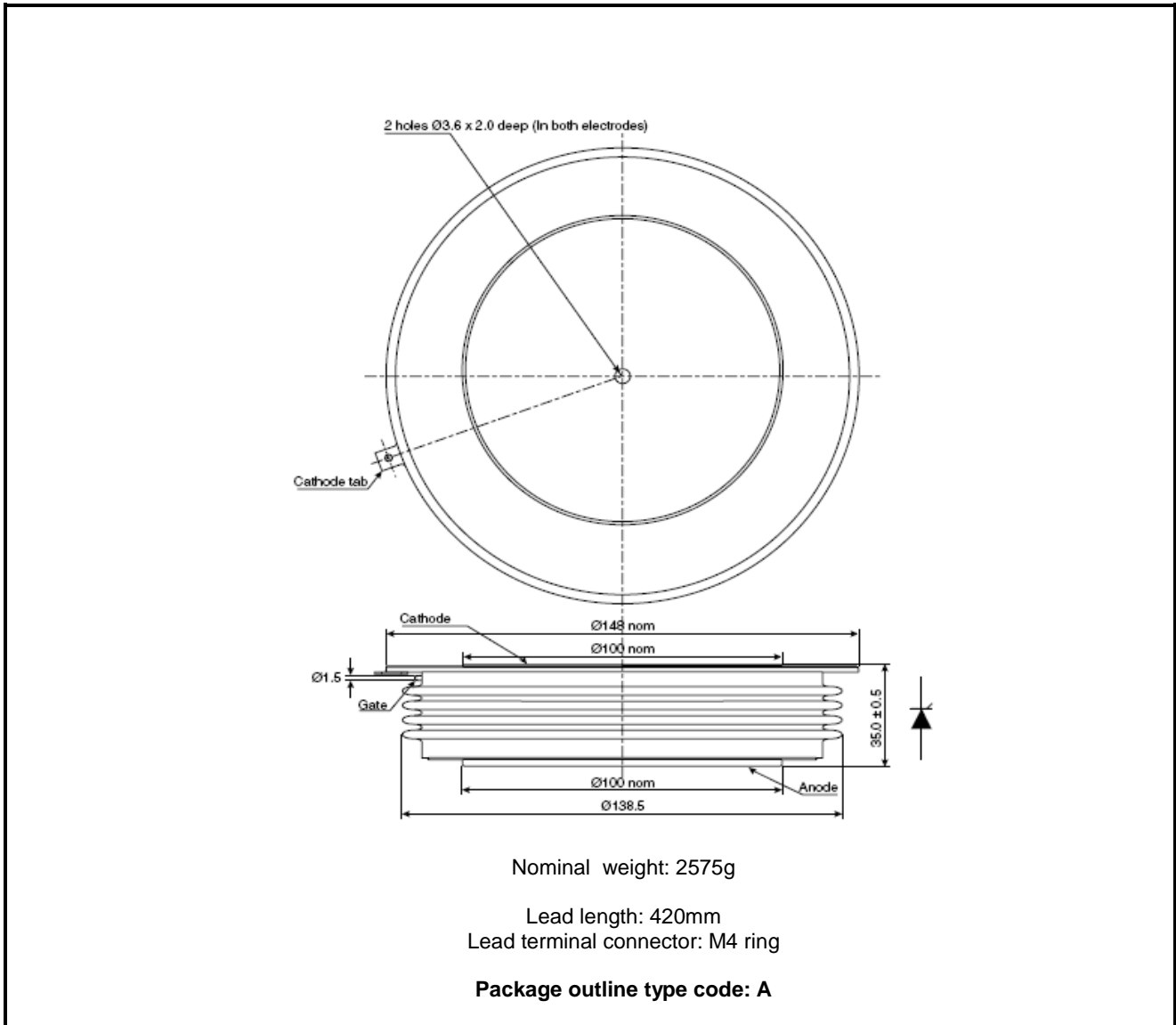


Fig.7 Package outline

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



<http://www.dynexsemi.com>

e-mail: power_solutions@dynexsemi.com

**HEADQUARTERS OPERATIONS
DYNEX SEMICONDUCTOR LTD**
Doddington Road, Lincoln
Lincolnshire, LN6 3LF. United Kingdom.
Tel: +44(0)1522 500500
Fax: +44(0)1522 500550

CUSTOMER SERVICE
Tel: +44(0)1522 502753 / 502901. Fax: +44(0)1522 500020

© Dynex Semiconductor 2003 TECHNICAL DOCUMENTATION – NOT FOR
RESALE. PRODUCED IN UNITED KINGDOM.

This publication is issued to provide information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose nor form part of any order or contract nor to be regarded as a representation relating to the products or services concerned. No warranty or guarantee express or implied is made regarding the capability, performance or suitability of any product or service. The Company reserves the right to alter without prior notice the specification, design or price of any product or service. Information concerning possible methods of use is provided as a guide only and does not constitute any guarantee that such methods of use will be satisfactory in a specific piece of equipment. It is the user's responsibility to fully determine the performance and suitability of any equipment using such information and to ensure that any publication or data used is up to date and has not been superseded. These products are not suitable for use in any medical products whose failure to perform may result in significant injury or death to the user. All products and materials are sold and services provided subject to the Company's conditions of sale, which are available on request.

All brand names and product names used in this publication are trademarks, registered trademarks or trade names of their respective owners.